

## 2nd Announcement

### Call for Papers

**8th International Symposium on  
Semiconductor Light Emitting Devices (ISSLED2010)**

**May 16-21, 2010, Beijing, China**



This symposium **aims** to provide a platform for scientists and engineers to discuss progress and future trends in the rapidly advancing wide bandgap semiconductor science and technologies, and their applications into visible and ultraviolet light emitting diodes and diode lasers.

The format of the symposium provides invited and contributed presentations during the meeting, followed by alternative tours of cultural and historic sceneries in Beijing.

The symposium will be a conference sharing the information among all participants, and memorable experience in China. It also establishes opportunities for the participants to exchange new ideas and application experiences, to establish research or business relations, and to find global partners for future collaboration.

### **Papers are solicited on a variety of topics including:**

- Materials Growth and Characterization
- Optoelectronic Properties
- Device Design and Fabrication
- Light Emitting Diodes
- Organic Light Emitting Diodes
- Laser Diodes
- Ultraviolet Emitters and Detectors
- Photonics
- Novel Optoelectronic Devices and Applications
- Device Performance and Reliability
- Spinoptronics and Spintronics
- Biological Applications
- Solar Cells and Sensors

### **Abstract Submission Guideline**

Prospective authors are requested to submit abstracts in English and the deadline changed to **March 15<sup>th</sup>, 2010**.

Online submission through the symposium website:

<http://www.issled2010.com.cn/> is

encouraged. The authors should pay attention to the following guidelines:

1. Acceptable format: Word.doc.
2. The abstract should be written by A4 paper with 2.5 cm margins on all sides.
3. The abstract should include the Title, Authors, Author affiliation, Main text and Keywords.
4. The title should be formatted using 14 point Arial. The main text should be formatted using 12 point Times New Roman. The text should be double spaced.
5. The length of the abstract text should not be longer than 150 words.

You may find out the **ISSLED Abstract Template** on the website helpful for your preparation.

### **The following are important dates pertinent to the conference:**

- ✦ **Abstract Submission Deadline: March 15<sup>th</sup>, 2010**
- ✦ **Notification of Acceptance: March 31<sup>st</sup>, 2010**
- ✦ **Early Registration Deadline: April 18<sup>th</sup>, 2010**
- ✦ **Late News Submission Deadline: May 9<sup>th</sup>, 2010**

For any query related to ISSLED2010, please email to:

**ISSLED2010@pku.edu.cn**

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## List of Invited Speakers (Under updating)

- Hiroshi Amano Meijo University, Japan  
*(Title: under updating)*
- Jim Speck, UCSB, USA  
*Progress in nonpolar and semipolar materials and devices*
- Armin Dadgar, University of Magdeburg, Germany  
*GaN on Si optoelectronics - status and challenges*
- Eva Monroy, CEA, France  
*New frontiers in GaN-based quantum devices for infrared optoelectronics*
- Martin Dawson, Strathclyde University, UK  
*AllnGaN micro-pixel light emitting diodes for instrumentation, optical communications and hybrid inorganic/organic optoelectronics*
- Y Kawakami, Kyoto, Japan  
*Mapping of efficiency droop in InGaN quantum wells studied by scanning near- field optical microscopy*
- Raphael Butte, EPFL Lausanne  
*Current status of AllnN layers and AllnN-based heterostructures nearly lattice-matched to GaN for photonics*
- Y. H. Cho, KAIST, Korea,  
*Optical characteristics and carrier dynamics of various ZnO epilayers and quantum structures*
- Cun-Zheng Ning, Arizona State University, USA  
*II-VI Semiconductor Alloy Nanowires for Full-Color Light Emitting and lasing*
- W. Walukiewicz, Lawrence Berkeley Laboratory, USA  
*Applications of III-nitrides for solar power conversion*
- Rong Zhang, Nanjing University, China  
*(Title: under updating)*
- David J. Smith, Arizona State University, USA  
*(Title: under updating)*
- J. L. Liu, University of California at Riverside, USA  
*Progress in ZnO-based Light Emitting Diodes*

- C.C. Yang, National Taiwan University  
*Surface Plasmon Coupled Light-emitting Diode - An Alternative Light-emitting Channel*
- Angelo J. Mascarenhas, National Renewable Energy Laboratory, USA  
*Green LEDs for color mixing white light using lattice-mismatched GaInP alloys*

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*We appreciate if you could kindly disseminate this information to your staffs and colleagues. We look forward to your participation in ISSLED2010.*

*Thank you and best regards!*

*Sincerely,*

*G. Y. Zhang (General chair of ISSLED 2010)  
X. D. Hu (Chair of Organizing of ISSLED 2010)*

